

ABSTRACT OF THE DISCLOSURE

Methods of patterning resists and structures including the patterned resists are disclosed. A patterned, multi-transmissive mask is used during patterning of resists to control exposure at areas of the resist at which features having different detail are desired. Exposure is varied in more finely patterned and more grossly patterned areas of the resist. The patterned resists have a high degree of topographical uniformity.